

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an ad experson



N-Channel QFET[®] MOSFET

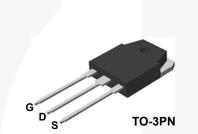
250 V, 62 A, 35 mΩ

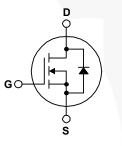
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- + 62 A, 250 V, $R_{DS(on)}$ = 35 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 31 A
- Low Gate Charge (Typ. 100 nC)
- Low Crss (Typ. 63.5 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter	FQA62N25C	Unit V	
V _{DSS}	Drain-Source Voltage	250		
I _D	Drain Current - Continuous (T _C = 25°C)	62	A	
	- Continuous (T _C = 100°C)	39	A	
I _{DM}	Drain Current - Pulsed (Note 1) 248	A	
V _{GSS}	Gate-Source Voltage	± 30	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2) 2300	mJ	
I _{AR}	Avalanche Current (Note 1) 62	A	
E _{AR}	Repetitive Avalanche Energy (Note 1	(Note 1) 29.8		
dv/dt	Peak Diode Recovery dv/dt (Note 3) 5.5	V/ns	
PD	Power Dissipation (T _C = 25°C)	298	W	
	- Derate above 25°C	2.38	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C	

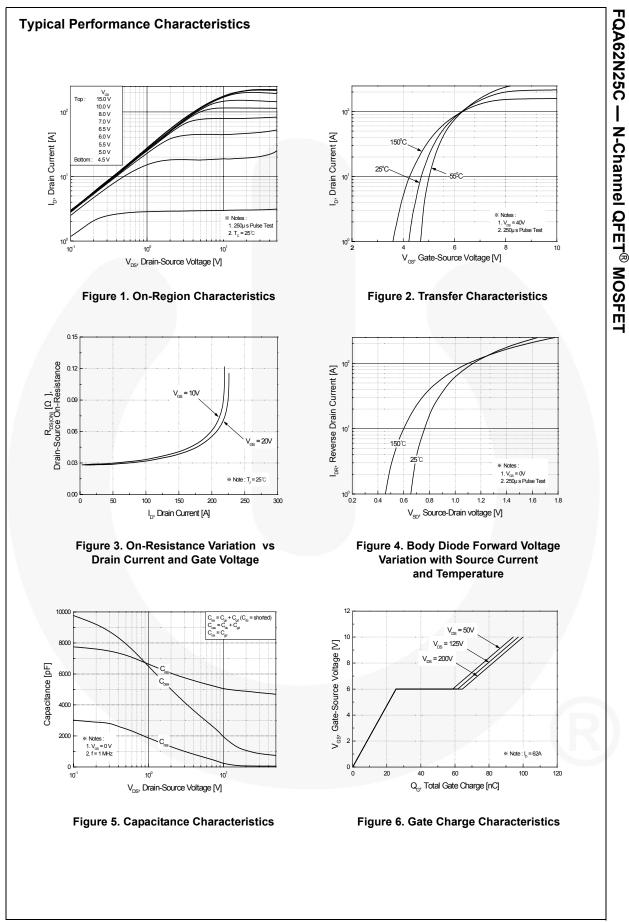
Thermal Characteristics

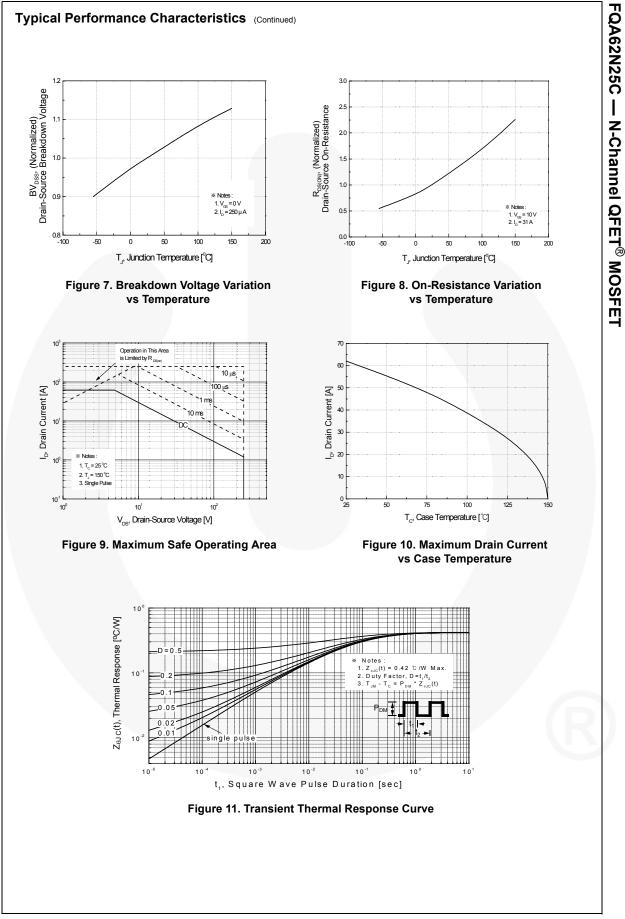
Symbol	Parameter	FQA62N25C	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

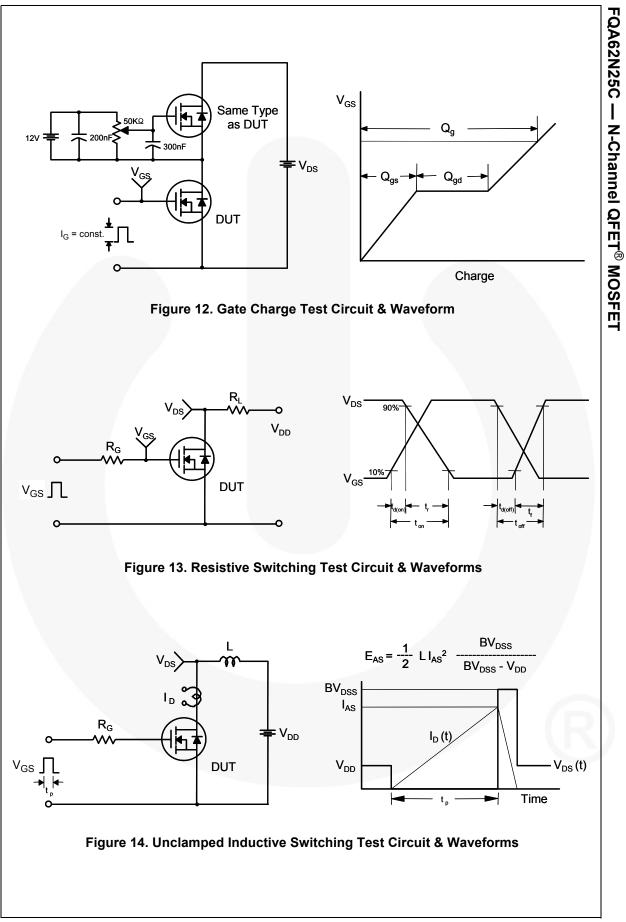
April 2014

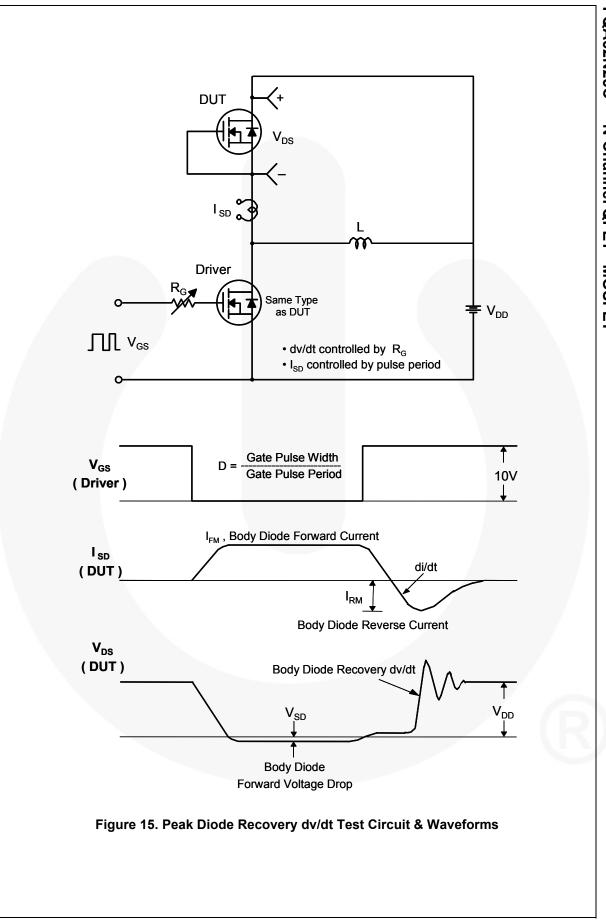
Part Nu	ımber	Top Mark	Pack	age Packing		g Method	Reel S	Size	Tape Width		Quantity
FQA62N25C		C FQA62N25C TO		3PN Tube N/		٩	N/A		30 units		
lootrid	al Ch	orootoriotioo	0								
Symbol		Parameter	Γ _C = 25°C unl	ess othen	wise noted. Test Con	ditions		Min.	Тур.	Max.	Unit
-		-4:								I	
BV _{DSS}	Drain-Se	stics ource Breakdown Vol	ane	Vcs =	= 0 V, I _D = 25	0 µA		250			V
ABV _{DSS}		Breakdown Voltage Temperature									
ΔT_{J}	Coefficient		$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$				0.28		V/°C		
DSS	Zero Gate Voltage Drain Current		V _{DS} = 250 V, V _{GS} = 0 V					10	μA		
			V _{DS} = 200 V, T _C = 125°C					100	μA		
GSSF		ody Leakage Current,		V_{GS} = 30 V, V_{DS} = 0 V					100	nA	
GSSR	Gate-Bo	ody Leakage Current,	Reverse	V _{GS} =	= -30 V, V _{DS}	= 0 V				-100	nA
On Cha	racteris	stics									
/ _{GS(th)}	1	reshold Voltage		V _{DS} =	= V _{GS} , I _D = 2	50 µA		2.0		4.0	V
R _{DS(on)}	Static Dr On-Resi	rain-Source istance		V _{GS} =	= 10 V, I _D = 31	A			0.029	0.035	Ω
FS	Forward	Transconductance	_	V _{DS} =	= 40 V, I _D = 3	1 A			55		S
viss voss vrss	Input Ca Output 0	acteristics apacitance Capacitance Transfer Capacitanc	e		= 25 V, V _{GS} = 0 MHz	: 0 V,			4830 945 63.5	6280 1230 83	pF pF pF
D ita h i		ve et e vietie e									
		Delay Time							75	160	ns
d(on) r		Rise Time	-		= 125 V, I _D =	62 A,			395	800	ns
d(off)		f Delay Time	-	R _G =	25 Ω				245	500	ns
f		f Fall Time	-				(Note 4)		335	680	ns
ג _מ	Total Ga	ate Charge		Vpc =	= 200 V, I _D =	62 A			100	130	nC
ק ג _{gs}		ource Charge			= 10 V	0274,			25.5		nC
ג ג ^{gd}	Gate-Dr	ain Charge					(Note 4)		39		nC
		Dia da Ohanaatan				- 4!					
s	1	Diode Character								62	A
S SM		m Pulsed Drain-Sour				•				248	A
/ _{SD}		ource Diode Forward			= 0 V, I _S = 62	A				1.5	V
rr		Recovery Time			= 0 V, I _S = 62				340		ns
ג גער	Reverse	Recovery Charge		00	it = 100 A/μs				4.77		μC
L = 0.96 mH I _{SD} ≤ 62 A, c	l, I _{AS} = 62 A, di/dt ≤ 300 A/	width limited by maximum ju $V_{DD} = 50 V$, $R_g = 25 \Omega$, star μ s, $V_{D} \le BV_{DSS}$, starting TJ of operating temperature.	ing T _J = 25°C								

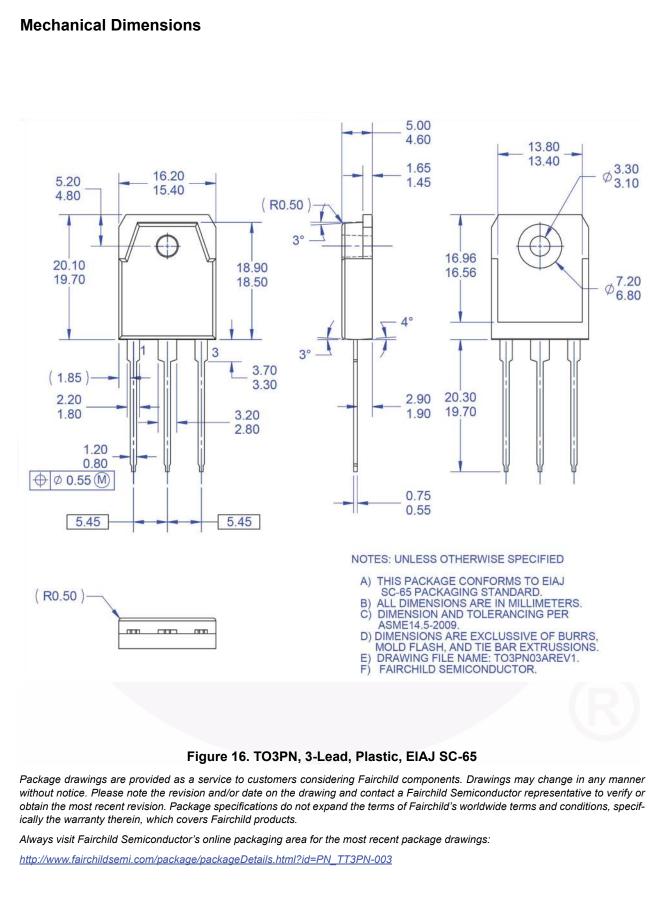
FQA62N25C — N-Channel QFET[®] MOSFET













ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC